

### THE INFLUENCE OF MBE GROWTH CONDITIONS ON OPTICAL PROPERTIES OF InAlGaAs/AlGaAs STRUCTURES

K. KOSIEL, K. REGIŃSKI, A. SZERLING, T. PIWOŃSKI, M. BUGAJSKI

Institute of Electron Technology, al. Lotników 32/46, 02-668 Warszawa, Poland

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#### ABSTRACT

Optical properties of compressively strained  $\text{In}_{0.24}\text{Al}_{0.19}\text{Ga}_{0.57}\text{As}$  layers were investigated as a function of the MBE growth conditions. The optimum temperature of the crystal surface ( $T_s$ ) for MBE growth of this quaternary layer as well as the optimal cooling down process necessary for achieving appropriate  $T_s$  for InAlGaAs were experimentally found.